

NO.1188D

LB1231 Series

High-Voltage, Large Current Darlington Transistor Array

The circuit configuration of this IC is of 7-channel Darlington transistor array consisting of NPN transistors. It is especially suited for use in hammer drivers and lamp, relay drivers. It contains spark killer diodes against L load.

Features High-voltage (VCEO≥50V), large-current (ICmax=500mA) drive

LB1231 . Drivable by TTL, MOS output

LB1232 . Contains base current limiting resistors, Zener diodes for

level shift.

. Direct drivable by 24V P MOS.

LB1233 . Contains base current limiting resistors.

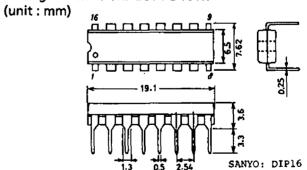
. Direct drivable by TTL, C MOS output.

LB1234 . Contains base current limiting resistors.

. Direct drivable by C MOS, P MOS output.

Absolute Maximum Ratings at Ta=25°C				
Output Supply Voltage			50	v
Output Current		Per unit	500	mΑ
Input Supply Voltage		LB1232/33/34	30	V
Input Current	I_{IN}	LB1231 only	25	mΑ
GND Pin Current		7ch simultaneously	on, 2.8	A
		f=10Hz,duty,=23%		
Allowable Power Dissipation	$P_{\mathbf{d}}$ max		1.5	W
Operating Temperature	Topr		-20 to +75	°C
Storage Temperature	Tstg		-40 to +150	°C
Allowable Operating Conditions at	: Ta=25°	С		unit
Output Supply Voltage Vou			50	v
Input "H" Level Voltage VIH	LB1232	$I_{OUT}=350mA$	11 to 30	V
	LB1233	IOUT=350mA	3 to 30	V
	LB1234	IOUT=350mA	5 to 30	V
Input "L" Level Voltage VIL	LB1231/	Aىر100¥100 33 33	-0.3 to $+0.3$	V
	LB1232	IOUT≦100μA	-0.3 to $+6.0$	V
	LB1234	IOUT≦100µA	-0.3 to $+0.7$	v

Package Dimensions 3064-D16TR

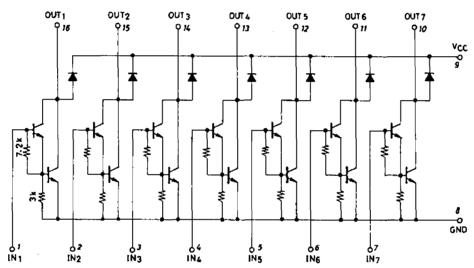


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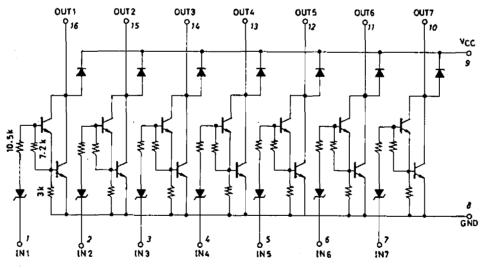
Electrical Characteristics at Ta=25°C			min	typ	max	unit	
Output Leak Current	IOFF	V _{OUT} =50V			100	Αιζ	
Output Voltage	$v_{\mathtt{OHl}}$	$I_{IN}=0.25$ mA, $I_{OUT}=100$ mA		0.9	1.1	v	
	v_{OH2}	$I_{IN}=0.35$ mA, $I_{OUT}=200$ mA		1.1	1.3	V	
	v_{OH3}	IIN=0.5mA, IOUT=350mA		1.3	1.6	V	
	VOH4	IIN=lmA, IOUT=400mA			2.4	v	
Input Voltage	v_{IN}	LB1231 I _{IN} =1mA		1.35	1.7	v	
Input Current	v_{IN}	LB1232 V _{IN} =17V		0.82	1.25	mA	
		LB1233 V _{IN} =3.85V		0.93	1.35	$\mathbf{m}\mathbf{A}$	
		LB1234 V _{IN} =5V		0.35	0.5	mA	
		LB1234 V _{IN} =12V		1.00	1.45	mA	
Spark Killer Diode Leak Currnet	IR(S)	$V_{R(S)}=50V$			100	Αιζ	
Spark Killer Diode 🗀 😗	$v_{\mathbf{F}(s)1}$	$I_{F(S)} = 350 \text{mA}$			2.0	v	
Forward Voltage	VF(S)2	$I_{F(S)} = 400 \text{mA}$			2.4	v	

Equivalent Circuits LB1231

Unit (resistance: Ω)



LB1232



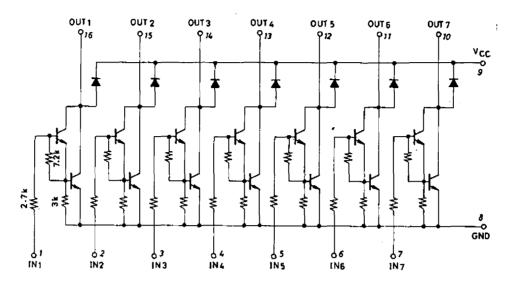
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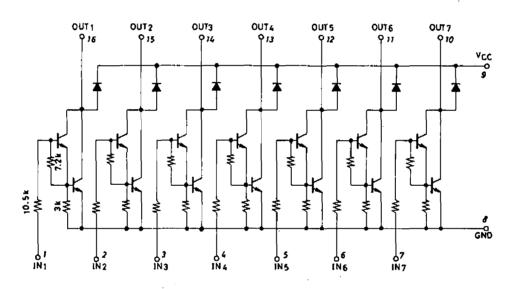
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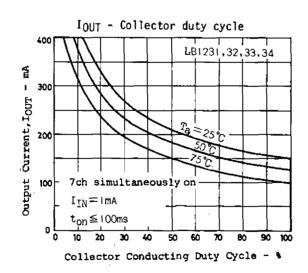
Unit (resistance: Ω)

LB1233



LB1234





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